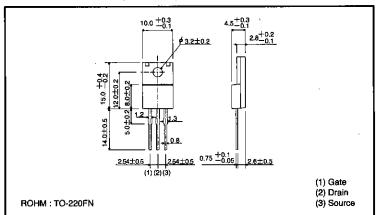
Features

- 1) Low on-resistance.
- 2) High-speed switching.
- 3) Wide SOA (safe operating area).
- 4) Gate-source voltage guaranteed at $V_{\text{GSS}} = \pm 30V$.
- 5) Easily designed drive circuits.
- 6) Easy to use in parallel.

Structure

Silicon N-channel MOSFET transistor

External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parame	eter	Symbol	Limits	Unit
Drain-source vo	ltage	Voss	250	٧
Gate-source vol	tage	V _{GSS}	±30	٧
D. N. S. S. S.	Continuous	lp	5	Α
Drain current	Pulsed	loe*	20	Α
Drain reverse	Continuous	lor	5	Α
current	Pulsed	IDRP*	20	A
Total power diss	ipation(Tc=25℃)	Po	30	W
Channel temper	ature	Tch	150	°
Storage tempera	ature	Tstg	−55~150	°

* Pw \leq 10 μ s, Duty cycle \leq 1%

Packaging specifications

	Package	Bulk	
Туре	Code	_	
	Basic ordering unit (pieces)	500	
2SK2460N		0	

AOS FET

ROHM

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate leakage current	lgss	_		±100	nA	V _{GS} =±30V, V _{DS} =0V
Drain-source breakdown voltage	V(BR)DSS	250	_	_	٧	lp=1mA, Vgs=0V
Drain cutoff current	loss	_	_	100	μΑ	V _{DS} =250V, V _{GS} =0V
Gate threshold voltage	VGS(th)	2	_	4	٧	Vos=10V, lo=1mA
Drain-source on-state resistance	RDS(on)	_	0.55	0.75	Ω	In=2.5A, Vgs=10V
Forward propagation admittance	Yts	2	3.5		s	V _{DS} =10V, I _D =2.5A
Input capacitance	Ciss		500	-	ρF	Vos=10V
Output capacitance	Coss		150		pF	V _{GS} =0
Reverse transfer capacitance	Crss	_	35	_	рF	f≂1MHz
Turn-on delay time	td(on)		7		ns	lb=2.5A, Vbb≒100V
Rise time	tr	_	15	_	ns	V _{GS} =10V
Turn-off delay time	t a(off)	_	30	_	ns	RL=40 Ω
Fall time	tr	_	25	_	ns	Rg=10Ω
Reverse recovery time	trr	_	150		ns	IDR=5A, VGS=0V
Reverse recovery load	Qır		0.7	_	μC	di/dt=100A/ μs

Electrical characteristic curves

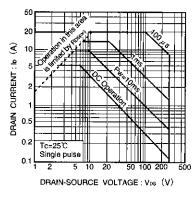


Fig.1 Maximum Safe Operating Area

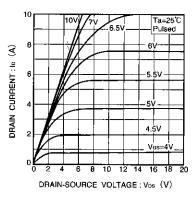


Fig.2 Typical Output Characteristics

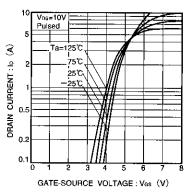


Fig.3 Typical Transfer Characteristics

Electrical characteristic curves

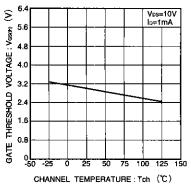


Fig.4 Gate Threshold Voltage vs. Channel Temperature

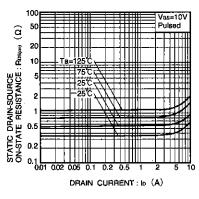


Fig.5 Static Drain-Source On-Resistance vs. Drain Current

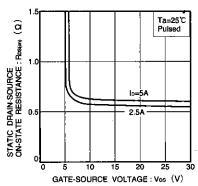


Fig.6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

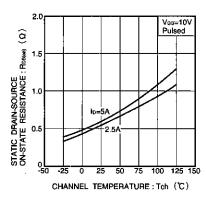


Fig.7 Static Drain-Source On-State Resistance vs. Channel Temperature

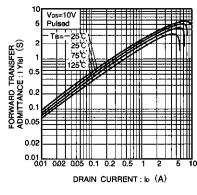


Fig.8 Forward Transfer Admittance vs. Drain Current

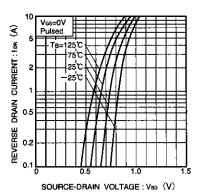


Fig.9 Reverse Drain Current vs. Source-Drain Voltage (I)

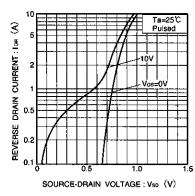


Fig.10 Reverse Drain Current vs. Source-Drain Voltage (II)

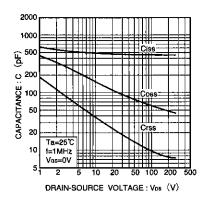


Fig.11 Typical Capacitance vs. Drain-Source Voltage

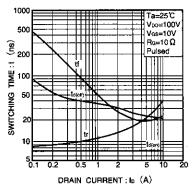
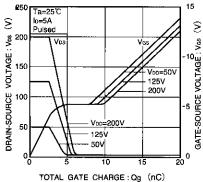


Fig.12 Switching Characteristics (See Figure. 16 and 17 for measurement circuits)

Electrical characteristic curves



TOTAL GATE CHARGE: Qg (nC)

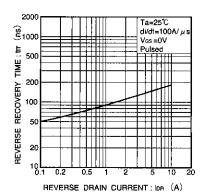
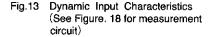


Fig.14 Rverse Recovery Time vs. Reverse Drain Current



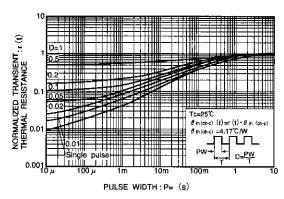


Fig.15 Normalized Transient Thermal Resistance Vs. Pulse Width

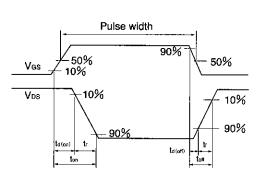


Fig.17 Switching Time Waveforms

Switching characteristics measurement circuit

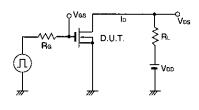


Fig.16 Switching Time Measurement Circuit

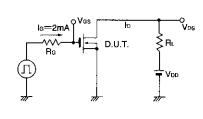


Fig.18 Gate Charge Measurement Circuit

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